NSN 5961-01-207-9573

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Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-207-9573 **Inclosure Material:** Ceramic and glass **Overall Length:** 0.115 inches **Overall Diameter:** 0.061 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Slot **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 collector to emitter voltage, dc and 7.0 emitter to collector voltage, dc **Current Rating Per Characteristic:** 3.00 microamperes emitter current, dc peak and 8.00 milliamperes peak forward surge current **Power Rating Per Characteristic:** 50.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 1 pin and 2 case Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli